

TO-92 Plastic-Encapsulate Transistors

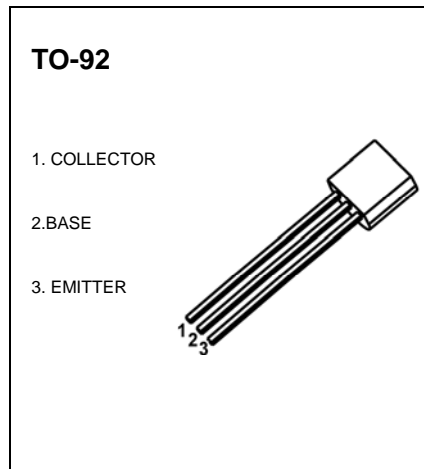
BC327/ BC328 TRANSISTOR (PNP)

FEATURES

- Power dissipation

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	BC327	-50
		BC328	-30
V _{CEO}	Collector-Emitter Voltage	BC327	-45
		BC328	-25
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-800	mA
P _C	Collector Power Dissipation	625	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



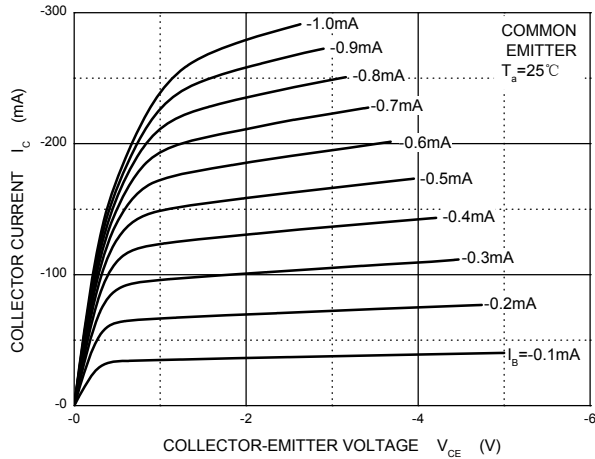
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = -100uA, I _E =0	-50			V
			-30			
Collector-emitter breakdown voltage	V _{CEO}	I _C = -10mA, I _B =0	-45			V
			-25			
Emitter-base breakdown voltage	V _{EBO}	I _E = -10uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -45 V, I _E =0 V _{CB} = -25V, I _E =0			-0.1	uA
					-0.1	
Collector cut-off current	I _{CEO}	V _{CE} = -40 V, I _B =0 V _{CE} = -20 V, I _B =0			-0.2	uA
					-0.2	
Emitter cut-off current	I _{EBO}	V _{EB} = -4 V, I _C =0			-0.1	uA
DC current gain	h _{FE(1)}	V _{CE} =-1 V, I _C = -100mA	100		630	
	h _{FE(2)}	V _{CE} =-1 V, I _C = -300mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B = -50mA			-0.7	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -500mA, I _B =-50mA			-1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =-1 V, I _C = -300mA			-1.2	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA f = 100MHz	260			MHz
Collector Output Capacitance	Cob	V _{CB} =-10V, I _E =0 f=1MHZ		12		pF

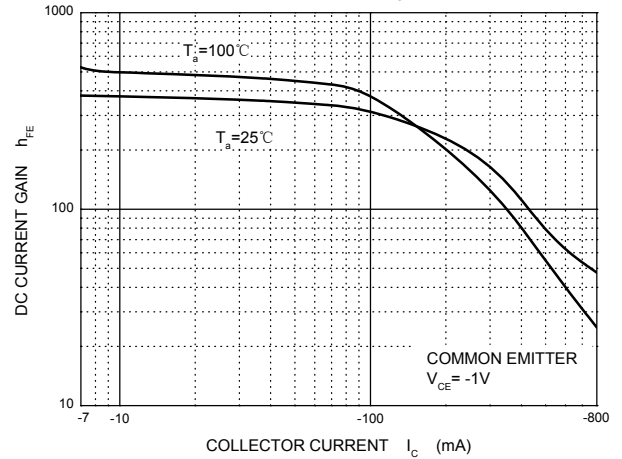
CLASSIFICATION OF h_{FE}

Rank	16	25	40
Range	100-250	160-400	250-630

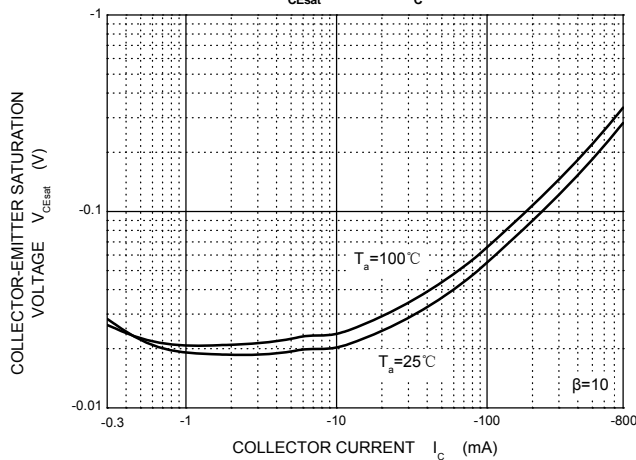
Static Characteristic



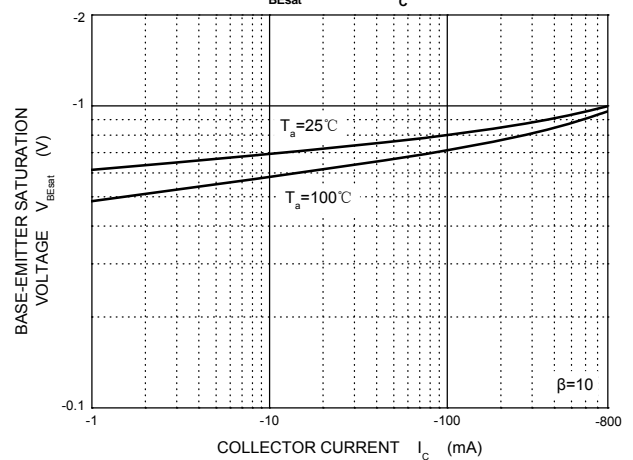
h_{FE} — I_c



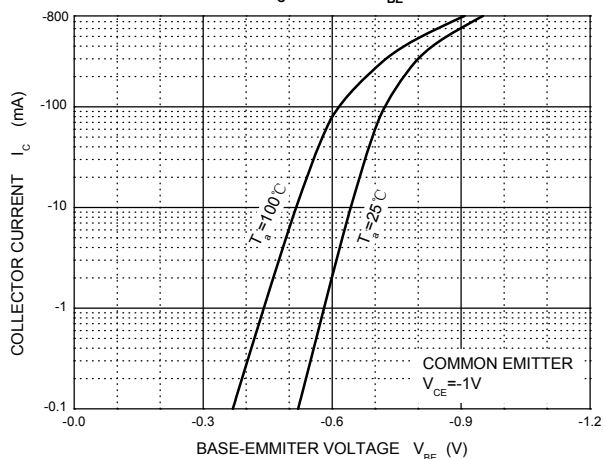
V_{CEsat} — I_c



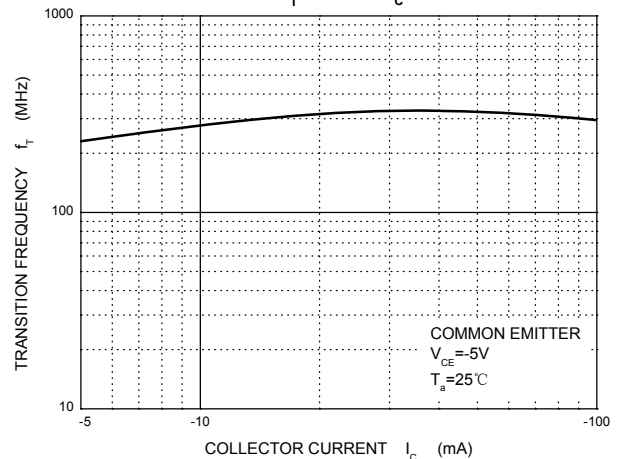
V_{BEsat} — I_c



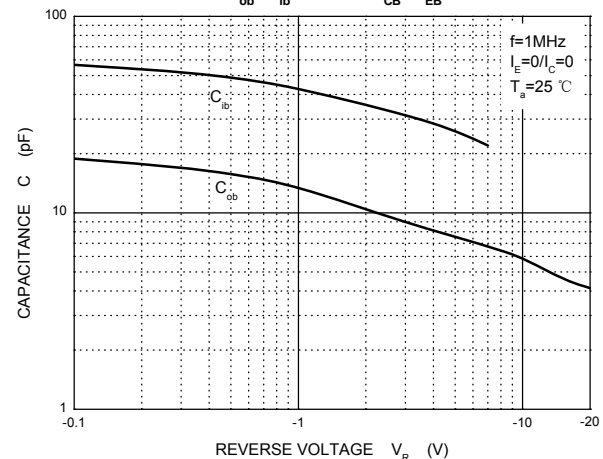
I_c — V_{BE}



f_T — I_c



C_{ob}/C_{ib} — V_{CB}/V_{EB}



P_c — T_a

